

● General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

● Features

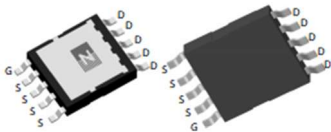
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low thermal resistance
- AEC-Q101 qualified

● Application

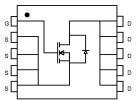
- BLDC motor driver
- DC-DC
- Load switch



● Product Summary



TCPAK5x7



$V_{DS}=100V$

$R_{DS(ON)}=2.6m\Omega$

$I_D=247A$



● Ordering Information

Part NO.	ZMSA026N10HTNC
Marking	26N10H
Packing information	REEL TAPE
Basic ordering unit (pcs)	2500

● Absolute Maximum Ratings ($T_A=25^\circ C$, unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Max.	Unit
Drain-source voltage	V_{DS}		-	100	V
Gate-source voltage ^①	V_{GS}		-20	20	V
Continuous drain current	I_D	$V_{GS}=10V, T_C=25^\circ C$	-	247	A
	I_D	$V_{GS}=10V, T_C=75^\circ C$	-	201	A
	I_D	$V_{GS}=10V, T_C=100^\circ C$	-	174	A
Pulsed drain current	I_{DM}	Pulsed; $t_p \leq 10 \mu s$; $T_C = 25^\circ C$;	-	988	A
Diode continuous current	I_S	$V_{GS}=0V, T_C=25^\circ C$	-	247	A
Diode pulse current	$I_{S,pulse}$	$V_{GS}=0V$, Pulsed, $t_p \leq 10 \mu s$, $T_C = 25^\circ C$	-	988	A
Total power dissipation	P_D	$T_C=25^\circ C$	-	417	W
Total power dissipation	P_D	$T_A=25^\circ C$	-	5	W
Operating junction temperature	T_J		-55	175	$^\circ C$
Storage temperature	T_{STG}		-55	175	$^\circ C$
Single pulse avalanche energy	E_{AS}	$L=0.1mH, V_{GS}=10V, R_g=25\Omega$,	-	339	mJ
		$L=0.5mH, V_{GS}=10V, R_g=25\Omega$,	-	610	mJ

ESD level (HBM)		CLASS 2
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● Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	0.36	°C/W
Thermal resistance, junction - ambient	$R_{thJA}^{\textcircled{2}}$	-	-	30	°C/W
Soldering temperature	T_{sold}	-	-	260	°C

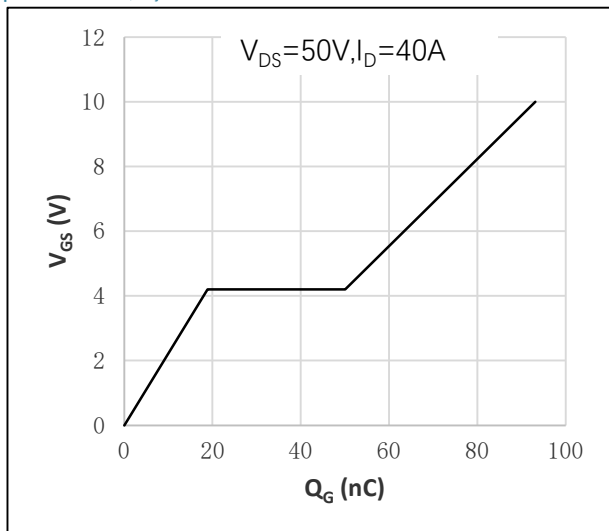
● Electronic Characteristics ($T_j=25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2	2.7	4	V
Drain-source leakage current	I_{DSS}	$V_{GS}=0V, V_{DS}=100V$	-	-	1	μA
Gate- source leakage current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	100	nA
Static drain-source on resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=40A, T_j=25^{\circ}\text{C}$	-	2.6	3.1	m Ω
		$V_{GS}=10V, I_D=40A, T_j=175^{\circ}\text{C}$	-	5.7	-	m Ω
Forward transconductance	g_{FS}	$V_{DS}=5V, I_{SD}=10A$	-	24	-	S
Diode forward voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=40A$	-	-	1.3	V

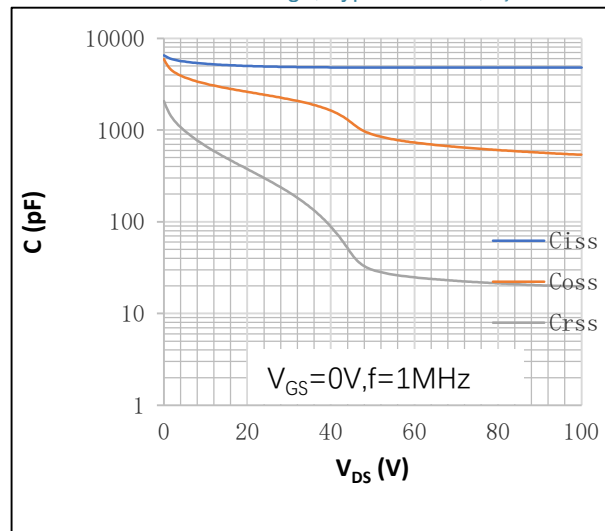
● Dynamic characteristics ($T_j=25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1\text{MHz}, V_{DS}=50V, V_{GS}=0V$	-	4820	-	pF
Output capacitance	C_{oss}		-	898	-	pF
Reverse transfer capacitance	C_{rss}		-	30	-	pF
Gate resistance	R_g	$f=1\text{MHz}$	-	0.6	-	Ω
Total gate charge	Q_g	$V_{DD}=50V, I_D=40A, V_{GS}=10V$	-	93.1	-	nC
Gate-source charge	Q_{gs}		-	18.9	-	nC
Gate-drain charge	Q_{gd}		-	31.2	-	nC
Turn-on delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=50V, R_G=3.3\Omega, I_D=40A$	-	14	-	ns
Turn-on rise time	t_r		-	8	-	ns
Turn-off delay time	$t_{D(off)}$		-	10	-	ns
Turn-off fall time	t_f		-	18	-	ns
Reverse recovery time	t_{rr}	$V_{DD}=50V, dI_S/dt=100A/\mu s, I_S=40A$	-	55	-	ns
Reverse recovery charge	Q_{rr}		-	50	-	nC

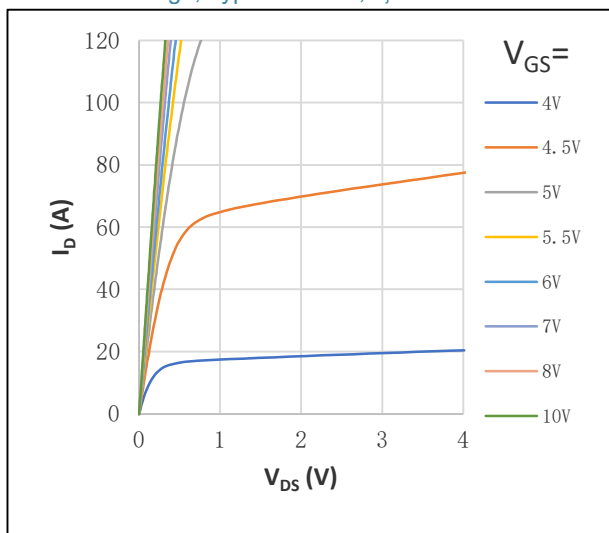
● Fig.1 Gate-source voltage as a function of gate charge; Typical values; $T_j=25^\circ\text{C}$



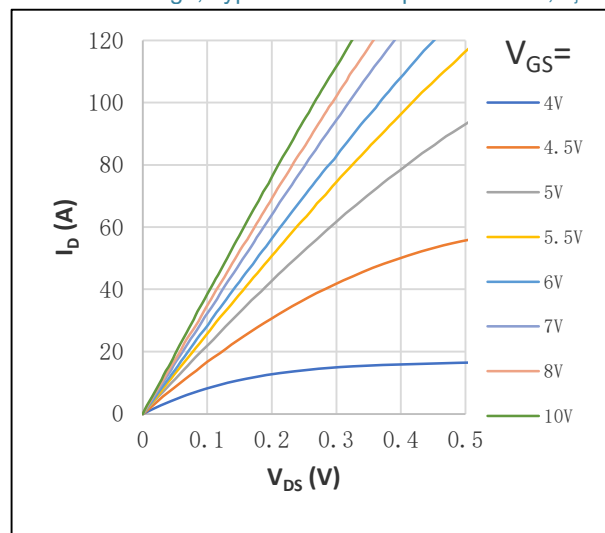
● Fig.2 Input, output and reverse transfer capacitances as a function of drain-source voltage; Typical values; $T_j=25^\circ\text{C}$



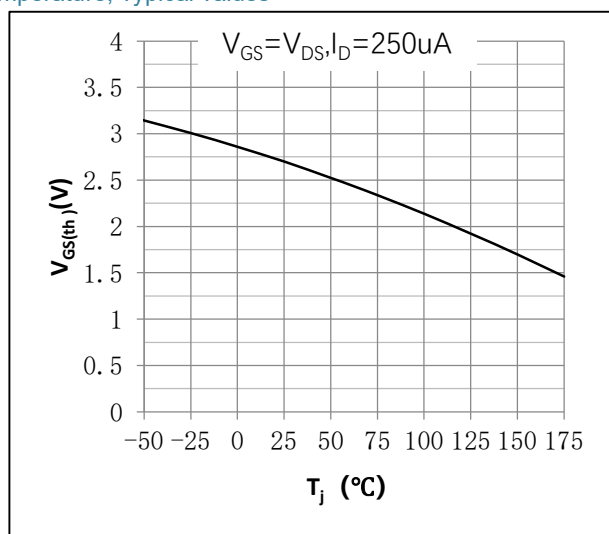
● Fig.3 Output characteristics: drain current as a function of drain-source voltage; Typical values; $T_j=25^\circ\text{C}$



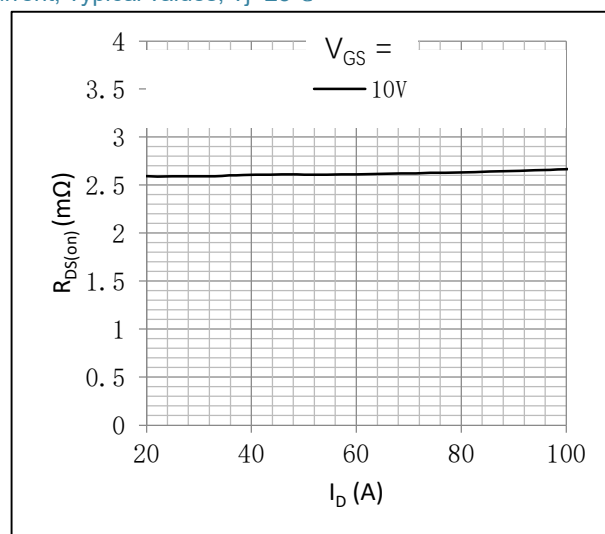
● Fig.4 Output characteristics: drain current as a function of drain-source voltage; Typical values: Expanded curve; $T_j=25^\circ\text{C}$



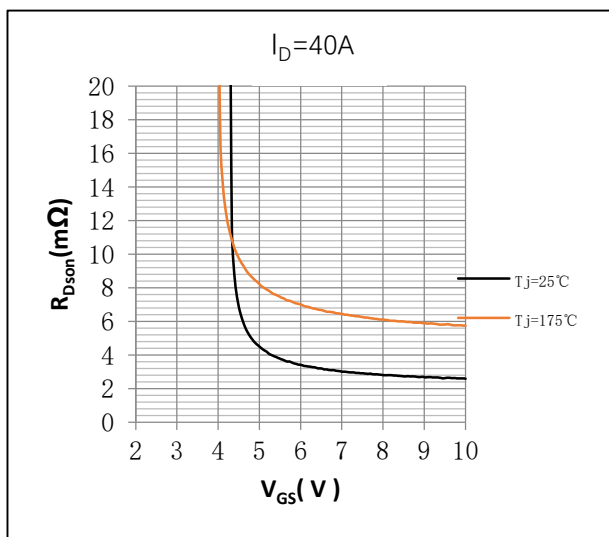
● Fig.5 Gate-source threshold voltage as a function of junction temperature; Typical values



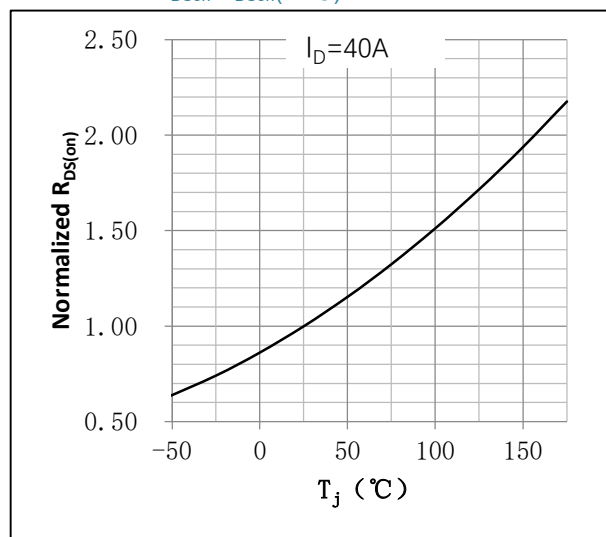
● Fig.6 Drain-source on-state resistance as a function of drain current; Typical values; $T_j=25^\circ\text{C}$



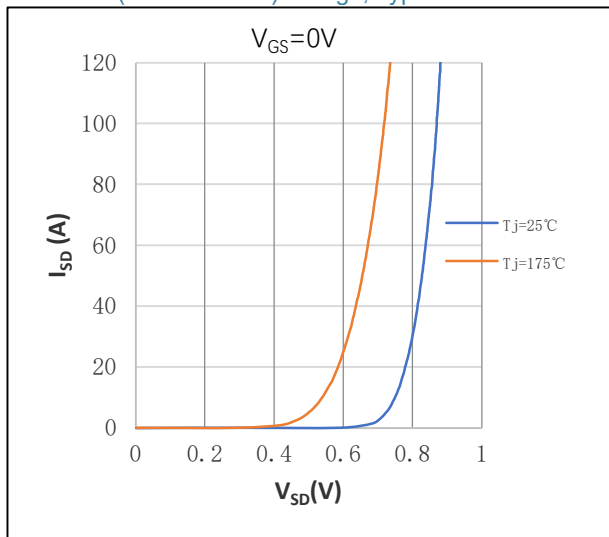
● Fig.7 Drain-source on-state resistance as a function of gate-source voltage; Typical values



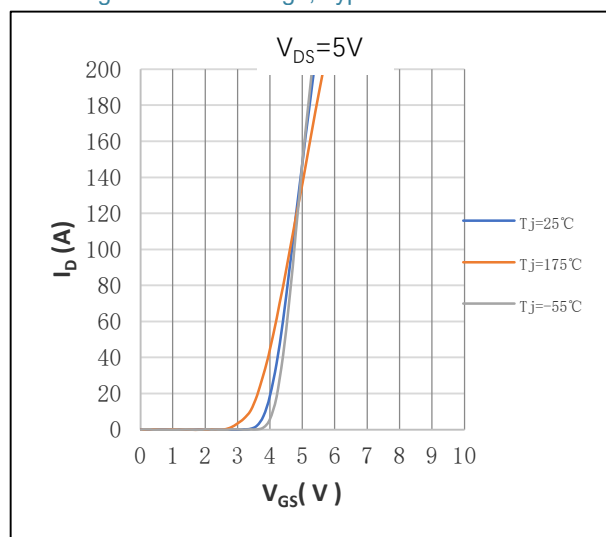
● Fig.8 Normalized drain-source on-state resistance factor as a function of junction temperature; Typical values Normalized On-Resistance = $R_{DS(on)}/R_{DS(on)}(25^{\circ}\text{C})$



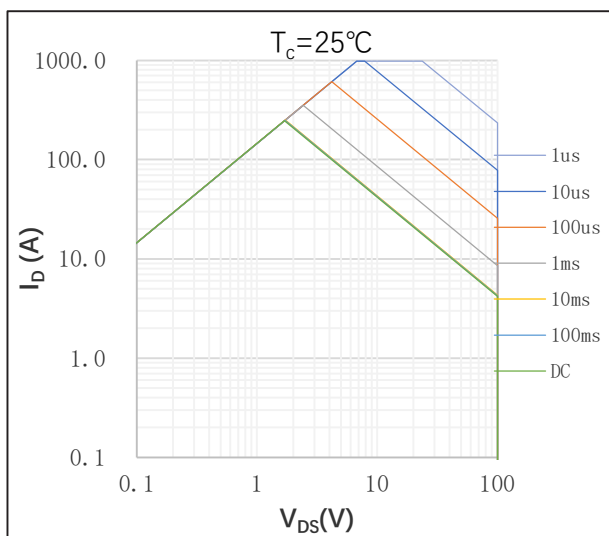
● Figure 9. Source (diode forward) current as a function of source-drain (diode forward) voltage; Typical values



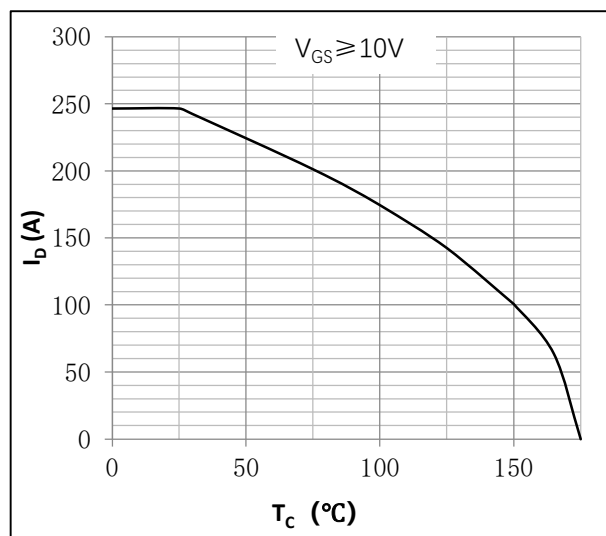
● Figure 10. Transfer characteristics: drain current as a function of gate-source voltage; Typical values



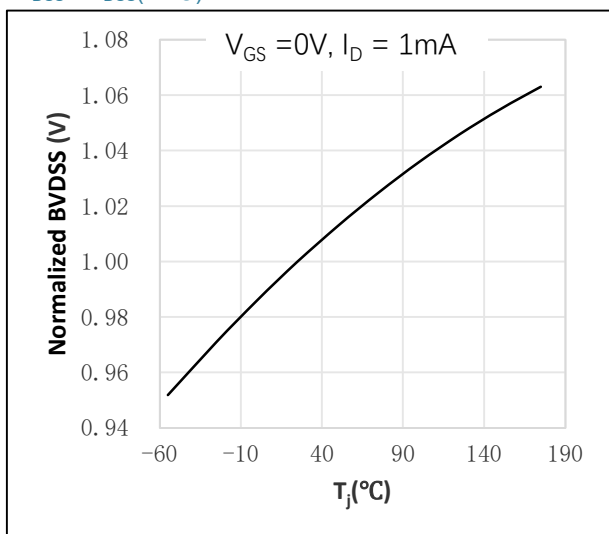
● Fig.11 Safe operating area: continuous and peak drain currents as a function of drain-source voltage; Calculative values



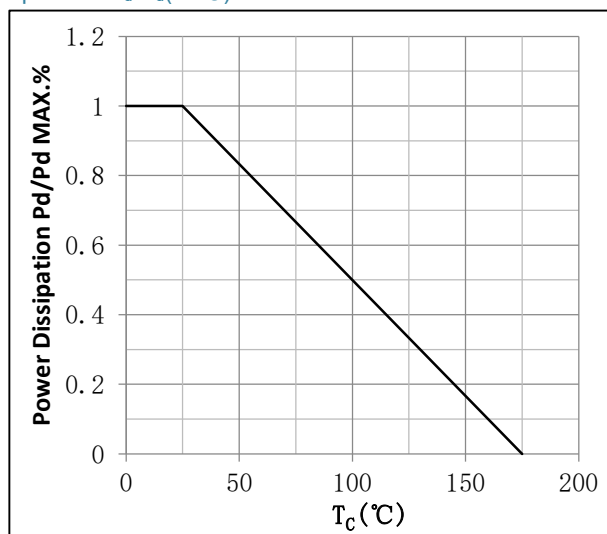
● Fig.12 Continuous drain current as a function of case temperature³; Calculative values



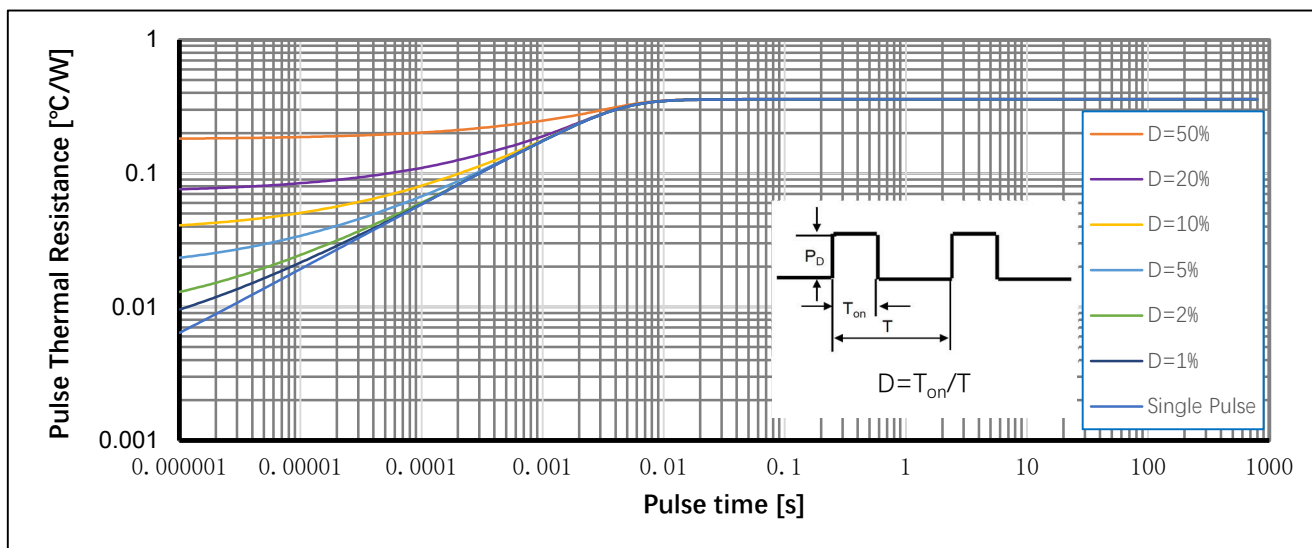
● Fig.13 Drain-source breakdown voltage as a function of junction temperature; Typical values Normalized $BV_{DSS} = BV_{DSS}/BV_{DSS}(25^{\circ}\text{C})$



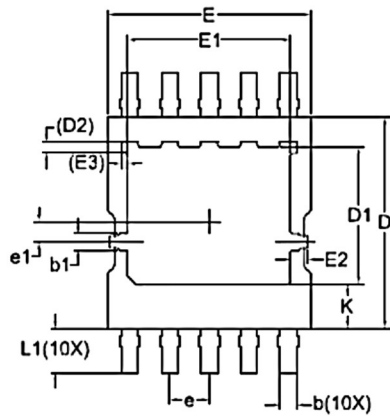
● Fig.14 Normalized total power dissipation as a function of case temperature; Calculative values Normalized Power Dissipation $= P_d/P_d(25^{\circ}\text{C})$



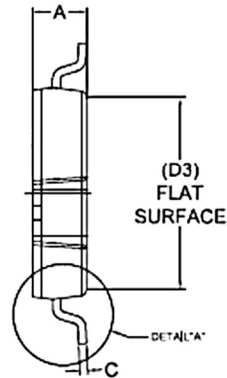
● Fig.15 Transient thermal impedance from junction to case as a function of pulse duration; max values



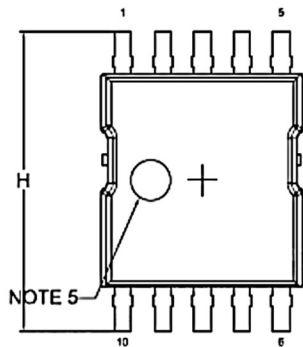
● Package Outline



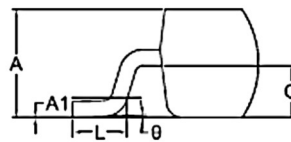
TOP VIEW



SIDE VIEW



BOTTOM VIEW


 DETAIL A*
(2:1)

MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.25	1.35	1.45
A1	-0.05	0	0.075
b	0.36	0.41	0.46
b1	0.30	0.40	0.50
c	0.16	0.20	0.26
D	5.20	5.30	5.40
D1	3.35	3.45	3.55
D2	0.29 REF		
D3	4.82 REF		
E	5.00	5.10	5.20
E1	4.02	4.12	4.22
E2	0.30	0.44	0.50
E3	0.14 REF		
e	1.00 BSC		
e1	0.50 BSC		
K	1.00	1.10	1.20
H	7.30	7.50	7.70
L	0.49	0.69	0.89
L1	0.90	1.10	1.30
Q	0.60	0.65	0.70
θ	0°	2.5°	5°

● Note

- ① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^{\circ}C$, $t=1000$ hours; For DC , the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^{\circ}C$, $t=1000$ hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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● Revision History

Version	Date	Change
A	2025/10/30	New